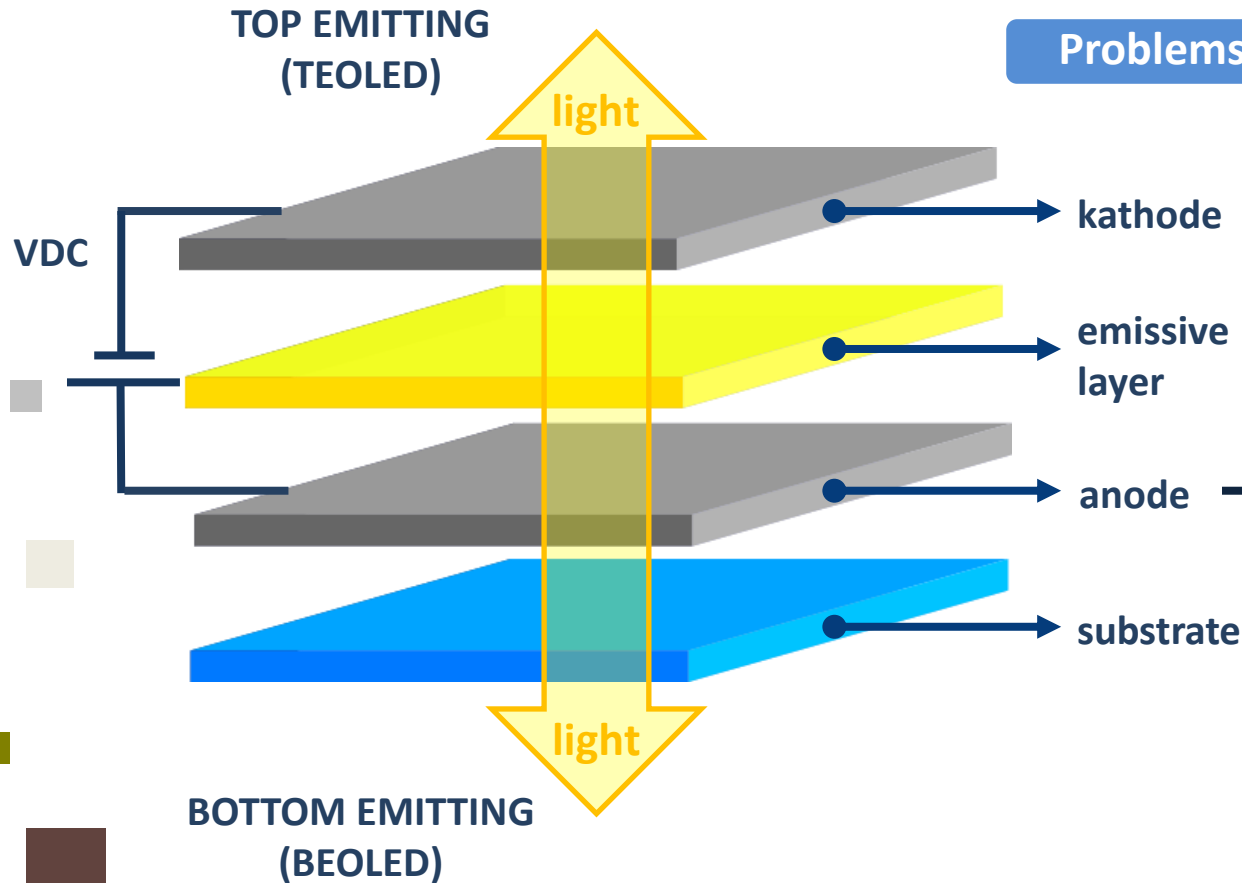


ITO-free transparent top electrode for top emitting OLEDs

Ing. Inge Verboven

Structure Organic Light Emitting Diode (OLED)



Problems with Indium thin Oxide (ITO)

ITO

- Expensive
- Crack formation
- Can not be a top electrode

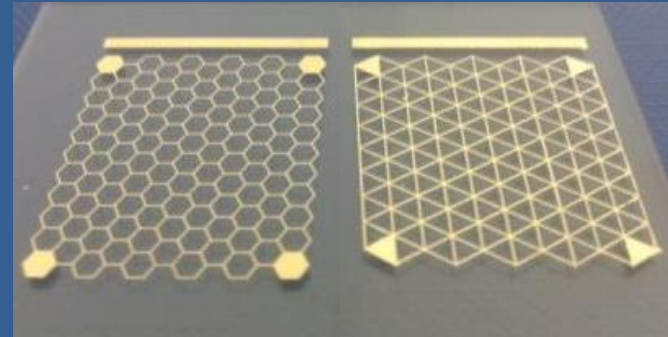
Semi transparent metal layers ↔ metal grids

Au layers



- ▶ Thermal evaporation
- ▶ Layer thickness 1-15 nm
- ▶ Sheet resistance 3,2-123,7 Ω/\square
- ▶ Transparency 25-70 %

Ag grids

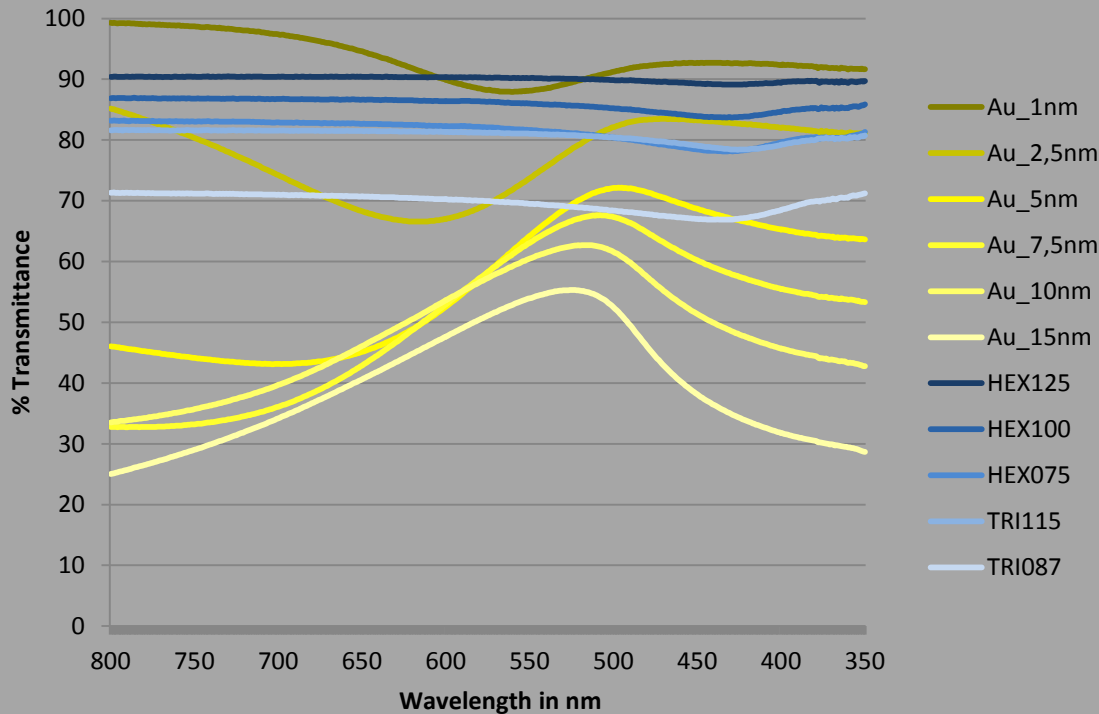


- ▶ Ink jet printing
- ▶ Layer thickness 150-250 nm
- ▶ Sheet resistance 0,82-2,7 Ω/\square
- ▶ Transparency 70-90 %



Semi transparent metal layers ↔ metal grids

Transmittance

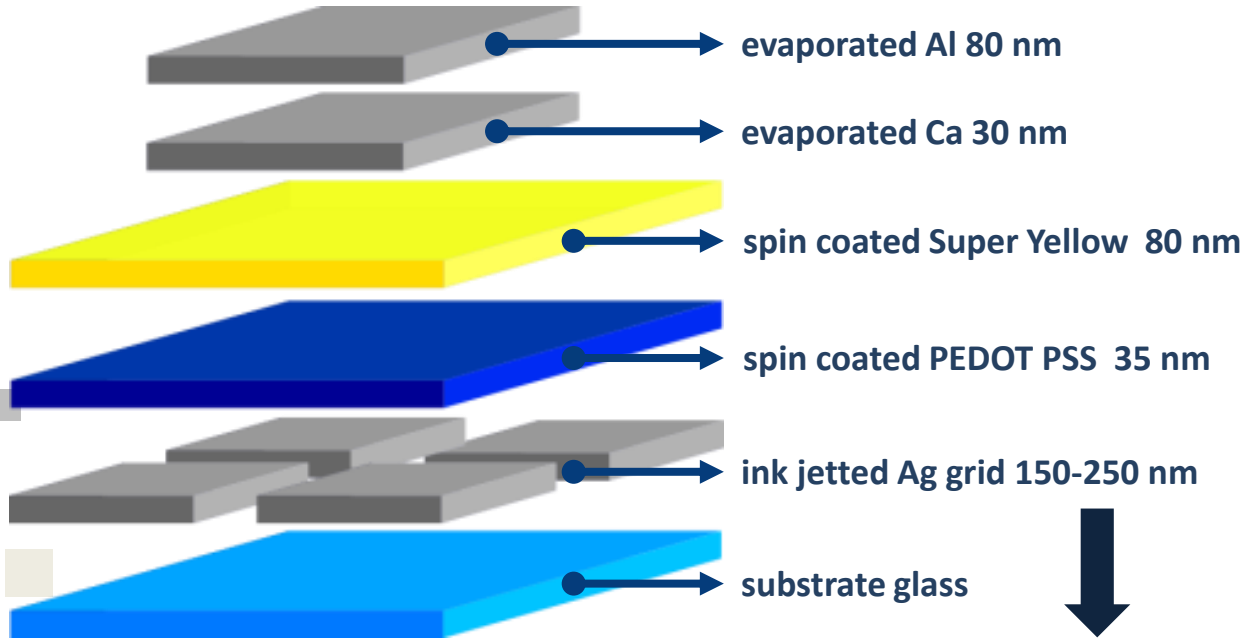


Conductivity

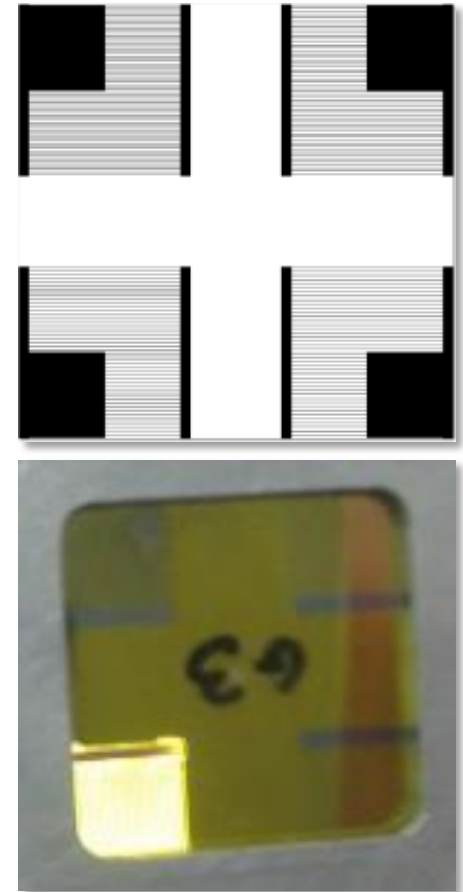
	Rs (Ω/\square)
HEX125	2,7
HEX100	1,5
HEX075	1,5
TRI115	1,2
TRI087	0,82
Au 1nm	> 20M
Au 2,5nm	> 20M
Au 5nm	> 20M
Au 7,5nm	123,7
Au 10nm	11,5
Au 15nm	3,2

BEOLED with Ag line grid

Testing of a BEOLED with Ag grid



↓
 Sintered at 200 °C
 Problem with TEOLED!
 Sintering damages other layers!





Conclusion

Au layers ↔ Ag grids

- Ag grids: higher transmittance, conductivity and less expensive and faster technique (ink jet printing)
 - Au layers: thinner and smoother layers
- Ag grid best option

BEOLED with Ag line grid

- Works
 - Lower light intensity and efficiency
- Optimization of structure and layer thickness necessary
- Sintering Ag grid without damaging other layers of TEOLED